

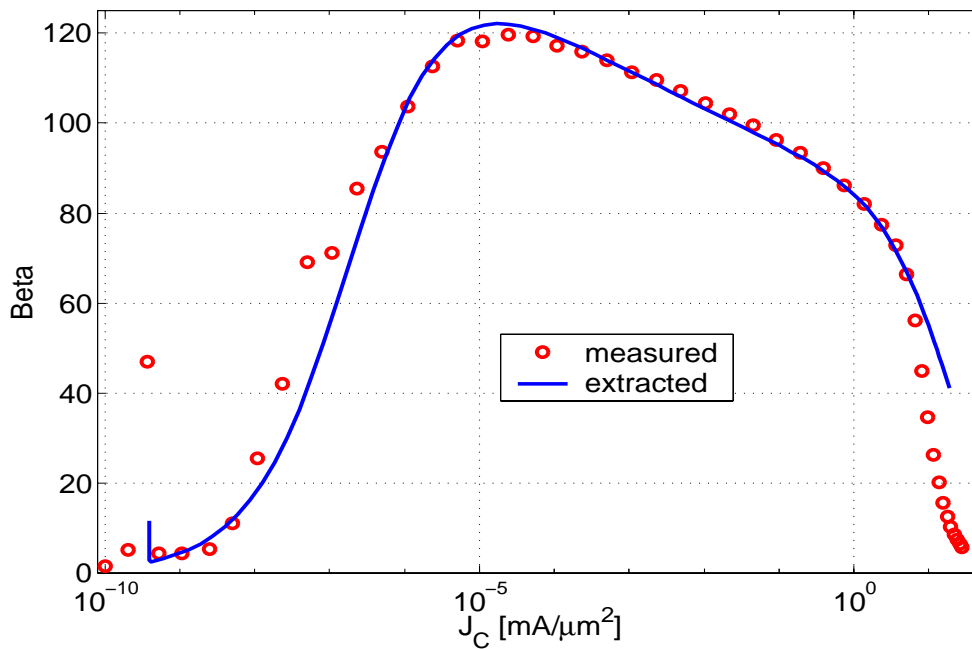
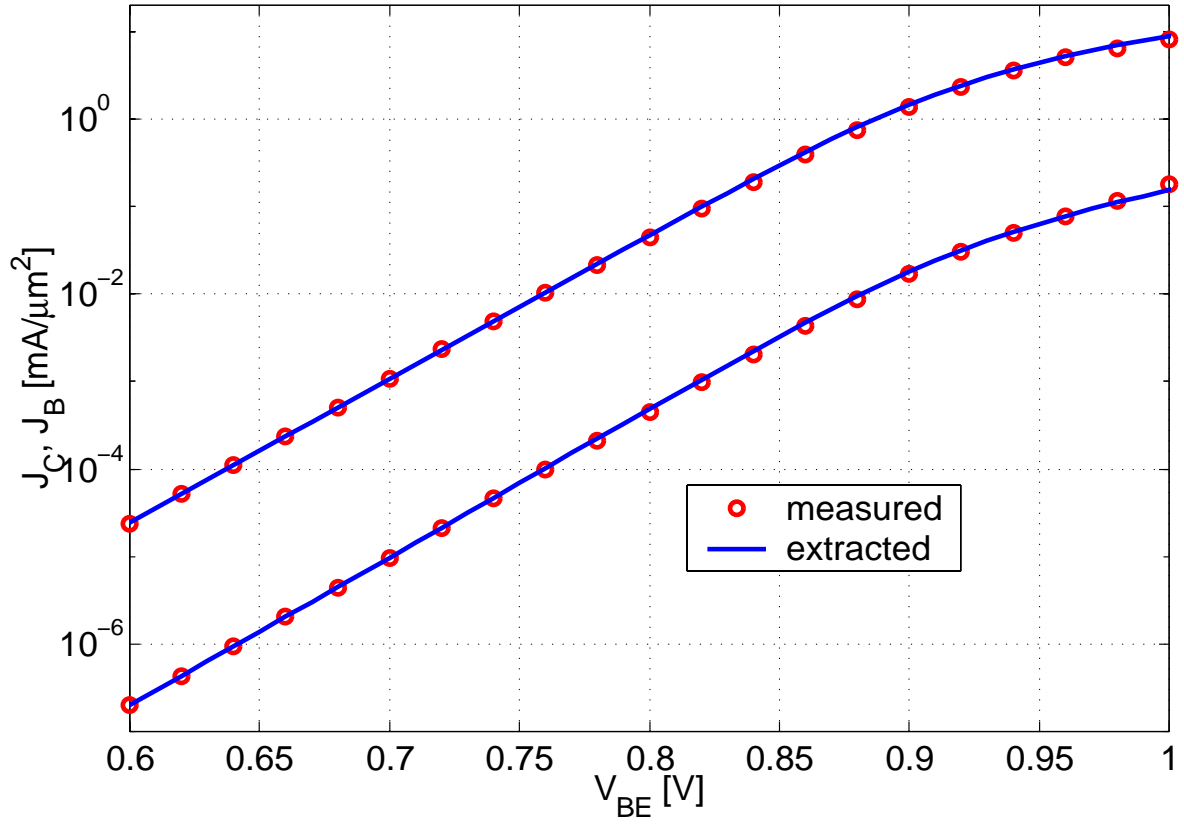
HICUM/Level0 model: more results

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- model overview see BCTM 2002 paper
- presented results are for Infineon's B7 SiGe HBT process technology
- parameter extraction performed on single geometry
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Forward characteristics

$A_{E0} = 0.25 \times 10.15 \mu\text{m}$, 27-Aug-2002; $V_{BC} = 0\text{V}$



output characteristics and f_T

$A_{E0} = 0.25 \times 10.15 \mu\text{m}$, 27-Aug-2002; $J_B = [12 \ 20 \ 31 \ 46 \ 77] \mu\text{A}$

